ABSTRACT

A memory and an electronic device are provided. The memory includes bit line functional groups spaced apart along a first direction, memory cells, a first staircase structure, and a second staircase structure located on a base substrate; each bit line functional group includes a first bit line, and a second bit line and a third bit line respectively coupled to the first bit line, the first bit line extending along a second direction, the second and third bit lines extending along a third direction; the second bit line and the memory cells are located on one side of the first bit line in the third direction, the third bit line and the first and second staircase structures are located on the other side of the first bit line in the third direction, and the first and second staircase structures are located on opposite sides of the third bit line.

[Fig. 2A]